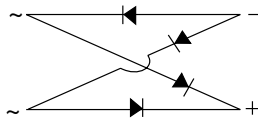


Miniature Glass Passivated Single-Phase Surface Mount Bridge Rectifiers



Case Style DFS

FEATURES

- UL recognition, file number E54214
- Ideal for automated placement
- High surge current capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 250 °C
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

TYPICAL APPLICATIONS

General purpose use in ac-to-dc bridge full wave rectification for SMPS, lighting ballaster, adapter, battery charger, home appliances, office equipment, and telecommunication applications.

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	1 A
V_{RRM}	50 V to 1000 V
I_{FSM}	50 A
I_R	5 μ A
V_F	1.1 V
T_J max.	150 °C

MECHANICAL DATA

Case: DFS

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Polarity: As marked on body

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	DF005S	DF01S	DF02S	DF04S	DF06S	DF08S	DF10S	UNIT
Device marking code		DF005S	DF01S	DF02S	DF04S	DF06S	DF08S	DF10S	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward output rectified current at $T_A = 40$ °C ⁽¹⁾	$I_{F(AV)}$	1.0							A
Peak forward surge current single half sine-wave superimposed on rated load	I_{FSM}	50							A
Rating for fusing ($t < 8.3$ ms)	I^2t	10							A ² s
Operating junction and storage temperature range	T_J, T_{STG}	- 55 to + 150							°C

Note:

(1) Units mounted on P.C.B. with 0.51 x 0.51" (13 x 13 mm) copper pads

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)										
PARAMETER	TEST CONDITIONS	SYMBOL	DF005S	DF01S	DF02S	DF04S	DF06S	DF08S	DF10S	UNIT
Maximum instantaneous forward voltage drop per diode	1.0 A	V_F					1.1			V
Maximum DC reverse current at rated DC blocking voltage per diode	$T_A = 25\text{ }^\circ\text{C}$ $T_A = 125\text{ }^\circ\text{C}$	I_R					5.0 500			μA
Typical junction capacitance per diode ⁽¹⁾		C_J					25			pF

Note:

(1) Measured at 1.0 MHz and applied reverse voltage of 4.0 V

THERMAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)										
PARAMETER	SYMBOL	DF005S	DF01S	DF02S	DF04S	DF06S	DF08S	DF10S	UNIT	
Typical thermal resistance ⁽¹⁾	$R_{\theta JA}$ $R_{\theta JL}$					40 15			$^\circ\text{C/W}$	

Note:

(1) Units mounted on P.C.B. with 0.51 x 0.51" (13 x 13 mm) copper pads

ORDERING INFORMATION (Example)				
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
DF06S-E3/45	0.399	45	50	Tube
DF06S-E3/77	0.399	77	1500	13" diameter paper tape and reel

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

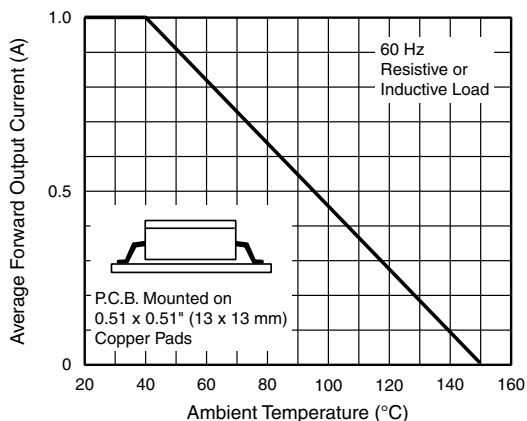


Figure 1. Derating Curve Output Rectified Current

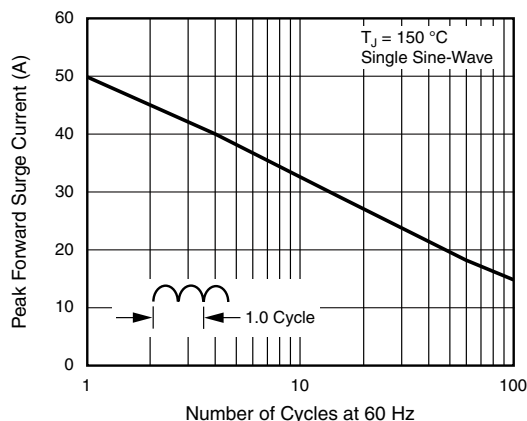


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

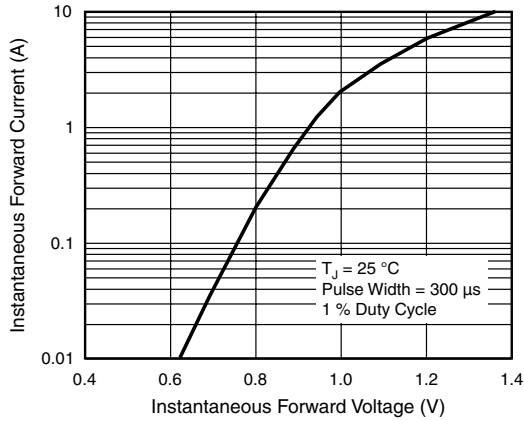


Figure 3. Typical Forward Characteristics Per Diode

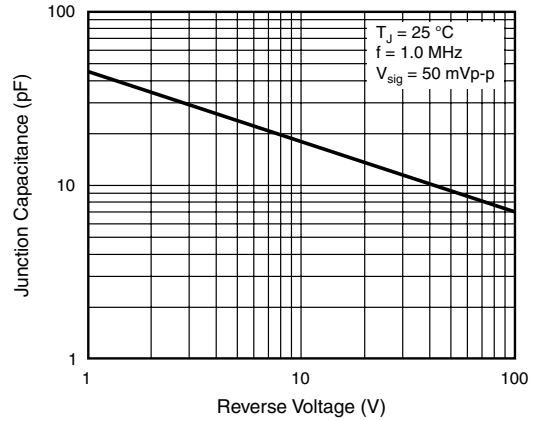


Figure 5. Typical Junction Capacitance Per Diode

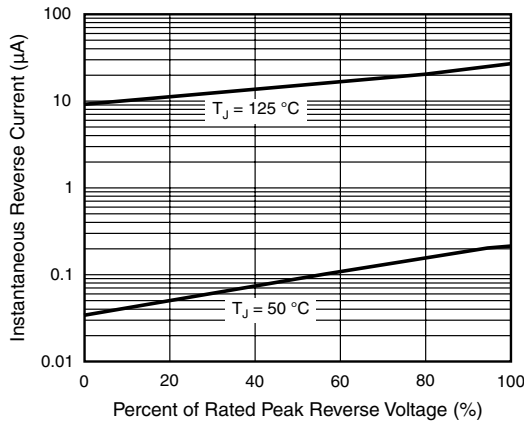


Figure 4. Typical Reverse Leakage Characteristics Per Diode

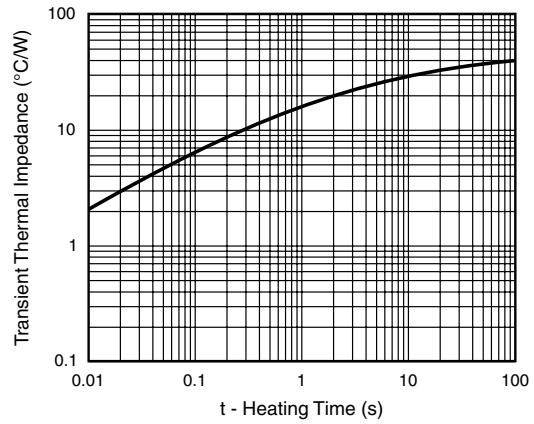


Figure 6. Typical Transient Thermal Impedance

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

